



PATENT  
98095

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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5-23-03*

In re application of:  
Gonzalez et al.

Group Art Unit: 2815

Examiner: Richards

Serial No. 09/144,662

Filed: September 1, 1998

SEMICONDUCTOR RAISED  
SOURCE-DRAIN STRUCTURE

DECLARATION UNDER 37 C.F.R. § 1.131

Commissioner for Patents  
Washington, D.C. 20231

Dear Commissioner:

We, Fernando Gonzalez and Chandra Mouli, declare as follows:

1. We are coinventors of all the claims of the above-identified patent application ("the subject application").
2. We are employed by Micron Technology Inc. ("Micron"), the assignee of the subject application.
3. All acts relied upon in establishing a date of invention prior to the March 2, 1998 reference date and reduction to practice were carried out in the United States of America.
4. Prior to March 2, 1998, we conceived the idea of utilizing air gaps with pocket junctions in a semiconductor raised source-drain structure.



VERSION WITH MARKINGS TO SHOW CHANGES MADE

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